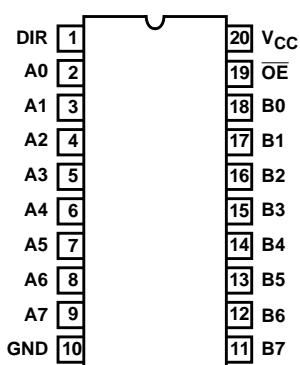


## Features

- Buffered Inputs
- Three-State Outputs
- Bus Line Driving Capability
- Typical Propagation Delay (A to B, B to A) 9ns at  $V_{CC} = 5V$ ,  $C_L = 15pF$ ,  $T_A = 25^\circ C$
- Fanout (Over Temperature Range)
  - Standard Outputs ..... 10 LSTTL Loads
  - Bus Driver Outputs ..... 15 LSTTL Loads
- Wide Operating Temperature Range ... -55°C to 125°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
  - 2V to 6V Operation
  - High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$  at  $V_{CC} = 5V$
- HCT Types
  - 4.5V to 5.5V Operation
  - Direct LSTTL Input Logic Compatibility,  $V_{IL} = 0.8V$  (Max),  $V_{IH} = 2V$  (Min)
  - CMOS Input Compatibility,  $I_I \leq 1\mu A$  at  $V_{OL}, V_{OH}$

## Pinout

**CD54HC245, CD54HCT245  
(CERDIP)**  
**CD74HC245, CD74HCT245  
(PDIP, SOIC)**  
 TOP VIEW



## Description

The CD54HC245, CD54HCT245, and CD74HC245, CD74HCT245 are high-speed octal three-state bidirectional transceivers intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation while driving large bus capacitances. They provide the low power consumption of standard CMOS circuits with speeds and drive capabilities comparable to that of LSTTL circuits.

The CD54HC245, CD54HCT245, CD74HC245 and CD74HCT245 allow data transmission of the B bus or from the B bus to the A bus. The logic level at the direction input (DIR) determines the direction. The output enable input (OE), when high, puts the I/O ports in the high-impedance state.

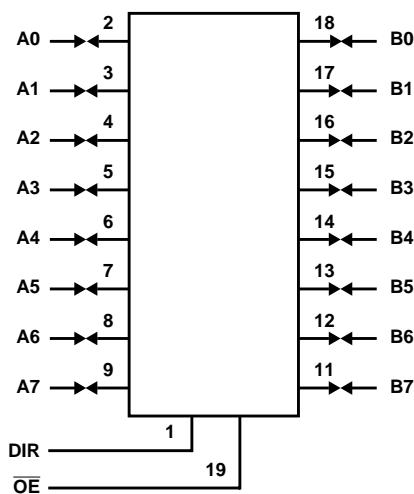
The HC/HCT245 is similar in operation to the HC/HCT640 and the HC/HCT643.

## Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC245F3A	-55 to 125	20 Ld CERDIP
CD54HCT245F3A	-55 to 125	20 Ld CERDIP
CD74HC245E	-55 to 125	20 Ld PDIP
CD74HC245M	-55 to 125	20 Ld SOIC
CD74HC245M96	-55 to 125	20 Ld SOIC
CD74HCT245E	-55 to 125	20 Ld PDIP
CD74HCT245M	-55 to 125	20 Ld SOIC
CD74HCT245M96	-55 to 125	20 Ld SOIC

NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and reel.

**Functional Diagram**



**TRUTH TABLE**

CONTROL INPUTS		OPERATION
OE	DIR	
L	L	B Data to A Bus
L	H	A Data to B Bus
H	X	Isolation

H = High Level, L = Low Level, X = Irrelevant

To prevent excess currents in the High-Z (Isolation) modes all I/O terminals should be terminated with  $10k\Omega$  to  $1M\Omega$  resistors.

# CD54HC245, CD74HC245, CD54HCT245, CD74HCT245

## Absolute Maximum Ratings

DC Supply Voltage, $V_{CC}$	.....	-0.5V to 7V
DC Input Diode Current, $I_{IK}$ For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	.....	$\pm 20mA$
DC Output Diode Current, $I_{OK}$ For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	.....	$\pm 20mA$
DC Drain Current, per Output, $I_O$ For $-0.5V < V_O < V_{CC} + 0.5V$	.....	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, $I_O$ For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	.....	$\pm 25mA$
DC $V_{CC}$ or Ground Current, $I_{CC}$	.....	$\pm 50mA$

## Thermal Information

Thermal Resistance (Typical, Note 1)	.....	$\theta_{JA}$ ( $^{\circ}C/W$ )
E (PDIP) Package	.....	69
M (SOIC) Package	.....	58
Maximum Junction Temperature	.....	150 $^{\circ}C$
Maximum Storage Temperature Range	.....	-65 $^{\circ}C$ to 150 $^{\circ}C$
Maximum Lead Temperature (Soldering 10s)	.....	300 $^{\circ}C$
(SOIC - Lead Tips Only)	.....	

## Operating Conditions

Temperature Range, $T_A$	.....	-55 $^{\circ}C$ to 125 $^{\circ}C$
Supply Voltage Range, $V_{CC}$	.....	
HC Types	.....	.2V to 6V
HCT Types	.....	.45V to 5.5V
DC Input or Output Voltage, $V_I, V_O$	.....	0V to $V_{CC}$
Input Rise and Fall Time	.....	
2V	.....	1000ns (Max)
4.5V	.....	500ns (Max)
6V	.....	400ns (Max)

**CAUTION:** Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

1. The package thermal impedance is calculated in accordance with JESD 51-7.

## DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		$V_{CC}$ (V)	25 $^{\circ}C$			-40 $^{\circ}C$ TO 85 $^{\circ}C$		-55 $^{\circ}C$ TO 125 $^{\circ}C$		UNITS		
		$V_I$ (V)	$I_O$ (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX			
<b>HC TYPES</b>														
High Level Input Voltage	$V_{IH}$	-	-	2	1.5	-	-	1.5	-	1.5	-	V		
				4.5	3.15	-	-	3.15	-	3.15	-	V		
				6	4.2	-	-	4.2	-	4.2	-	V		
Low Level Input Voltage	$V_{IL}$	-	-	2	-	-	0.5	-	0.5	-	0.5	V		
				4.5	-	-	1.35	-	1.35	-	1.35	V		
				6	-	-	1.8	-	1.8	-	1.8	V		
High Level Output Voltage CMOS Loads	$V_{OH}$	$V_{IH}$ or $V_{IL}$	-0.02	2	1.9	-	-	1.9	-	1.9	-	V		
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V		
			-0.02	6	5.9	-	-	5.9	-	5.9	-	V		
High Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V		
			-4	4.5	3.98	-	-	3.84	-	3.7	-	V		
			-5.2	6	5.48	-	-	5.34	-	5.2	-	V		
Low Level Output Voltage CMOS Loads	$V_{OL}$	$V_{IH}$ or $V_{IL}$	0.02	2	-	-	0.1	-	0.1	-	0.1	V		
			0.02	4.5	-	-	0.1	-	0.1	-	0.1	V		
			0.02	6	-	-	0.1	-	0.1	-	0.1	V		
Low Level Output Voltage TTL Loads			-	-	-	-	-	-	-	-	-	V		
			4	4.5	-	-	0.26	-	0.33	-	0.4	V		
			5.2	6	-	-	0.26	-	0.33	-	0.4	V		
Input Leakage Current	$I_I$	$V_{CC}$ or GND	-	6	-	-	$\pm 0.1$	-	$\pm 1$	-	$\pm 1$	$\mu A$		
Quiescent Device Current	$I_{CC}$	$V_{CC}$ or GND	0	6	-	-	8	-	80	-	160	$\mu A$		

# CD54HC245, CD74HC245, CD54HCT245, CD74HCT245

## DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V <sub>CC</sub> (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V <sub>I</sub> (V)	I <sub>O</sub> (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	6	-	-	±0.5	-	±5	-	±10	µA
<b>HCT TYPES</b>												
High Level Input Voltage	V <sub>IH</sub>	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V <sub>IL</sub>	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V <sub>OH</sub>	V <sub>IH</sub> or V <sub>IL</sub>	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-4	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V <sub>OL</sub>	V <sub>IH</sub> or V <sub>IL</sub>	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			4	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I <sub>I</sub>	V <sub>CC</sub> and GND	0	5.5	-	-	±0.1	-	±1	-	±1	µA
Quiescent Device Current	I <sub>CC</sub>	V <sub>CC</sub> or GND	0	5.5	-	-	8	-	80	-	160	µA
Three-State Leakage Current	I <sub>OZ</sub>	V <sub>IL</sub> or V <sub>IH</sub>	V <sub>O</sub> = V <sub>CC</sub> or GND	6	-	-	±0.5	-	±5	-	±10	µA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI <sub>CC</sub> (Note 2)	V <sub>CC</sub> -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	µA

NOTE:

2. For dual-supply systems theoretical worst case (V<sub>I</sub> = 2.4V, V<sub>CC</sub> = 5.5V) specification is 1.8mA.

## HCT Input Loading Table

INPUT	UNIT LOADS
A <sub>n</sub> or B <sub>n</sub>	0.4
OE	1.5
DIR	0.9

NOTE: Unit Load is ΔI<sub>CC</sub> limit specified in DC Electrical Table, e.g., 360µA max at 25°C.

# CD54HC245, CD74HC245, CD54HCT245, CD74HCT245

## Switching Specifications $C_L = 50\text{pF}$ , Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	$V_{CC} (\text{V})$	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
				MIN	TYP	MAX	MIN	MAX	MIN	MAX	
<b>HC TYPES</b>											
Propagation Delay Data to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	2	-	-	110	-	140	-	165	ns
			4.5	-	-	22	-	28	-	33	ns
		$C_L = 15\text{pF}$	5	-	9	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	19	-	24	-	28	ns
Output Disable to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	26	-	33	-	38	ns
Output Enable to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	2	-	-	150	-	190	-	225	ns
			4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	-	26	-	33	-	38	ns
Output Transition Time	$t_{THL}, t_{TLH}$	$C_L = 50\text{pF}$	2	-	-	60	-	75	-	90	ns
			4.5	-	-	12	-	15	-	18	ns
			6	-	-	10	-	13	-	15	ns
Input Capacitance	$C_{IN}$	$C_L = 50\text{pF}$	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	$C_{PD}$	-	5	-	53	-	-	-	-	-	pF
<b>HCT TYPES</b>											
Propagation Delay Data to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	4.5	-	-	26	-	33	-	39	ns
		$C_L = 15\text{pF}$	5	-	10	-	-	-	-	-	ns
Output Disable to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	4.5	-	-	30	-	38	-	45	ns
		$C_L = 15\text{pF}$	5	-	12	-	-	-	-	-	ns
Output Enable to Output	$t_{PHL}, t_{PLH}$	$C_L = 50\text{pF}$	4.5	-	-	32	-	40	-	48	ns
		$C_L = 15\text{pF}$	5	-	13	-	-	-	-	-	ns
Output Transition Time	$t_{THL}, t_{TLH}$	$C_L = 50\text{pF}$	4.5	-	-	12	-	15	-	18	ns
Input Capacitance	$C_{IN}$	$C_L = 50\text{pF}$	-	10	-	10	-	10	-	10	pF
Three-State Output Capacitance	$C_O$	-	-	-	-	20	-	20	-	20	pF
Power Dissipation Capacitance (Notes 3, 4)	$C_{PD}$	-	5	-	55	-	-	-	-	-	pF

### NOTES:

3.  $C_{PD}$  is used to determine the dynamic power consumption, per channel.
4.  $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$  where  $f_i$  = Input Frequency,  $C_L$  = Output Load Capacitance,  $V_{CC}$  = Supply Voltage.

### Test Circuits and Waveforms

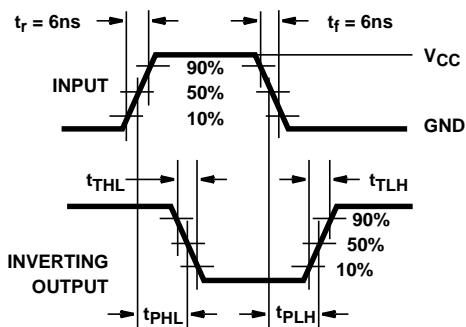


FIGURE 1. HC TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

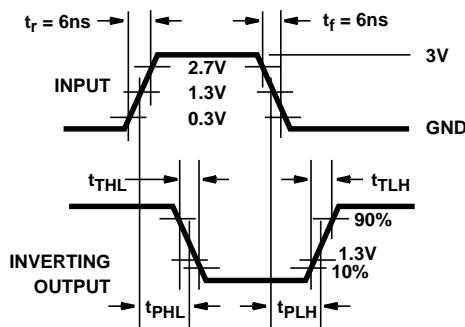


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

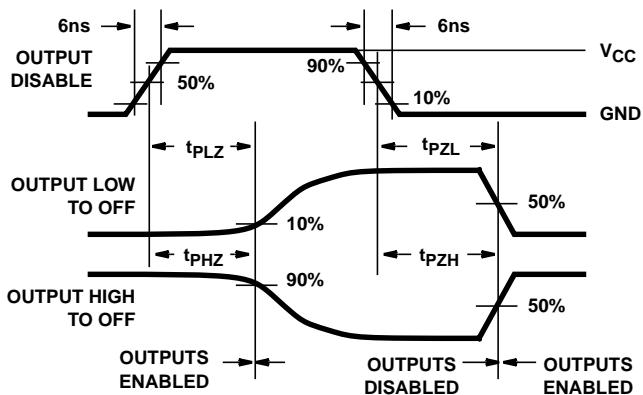


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

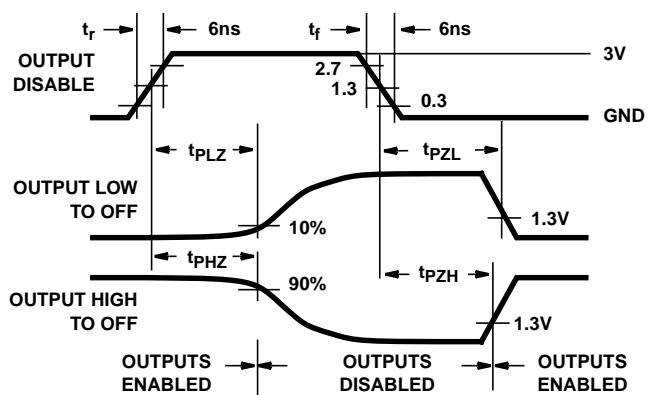
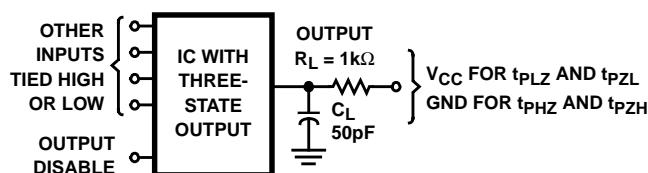


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms  $t_{PLZ}$  and  $t_{PZL}$  are the same as those for three-state shown on the left. The test circuit is Output  $R_L = 1\text{k}\Omega$  to  $V_{CC}$ ,  $C_L = 50\text{pF}$ .

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT